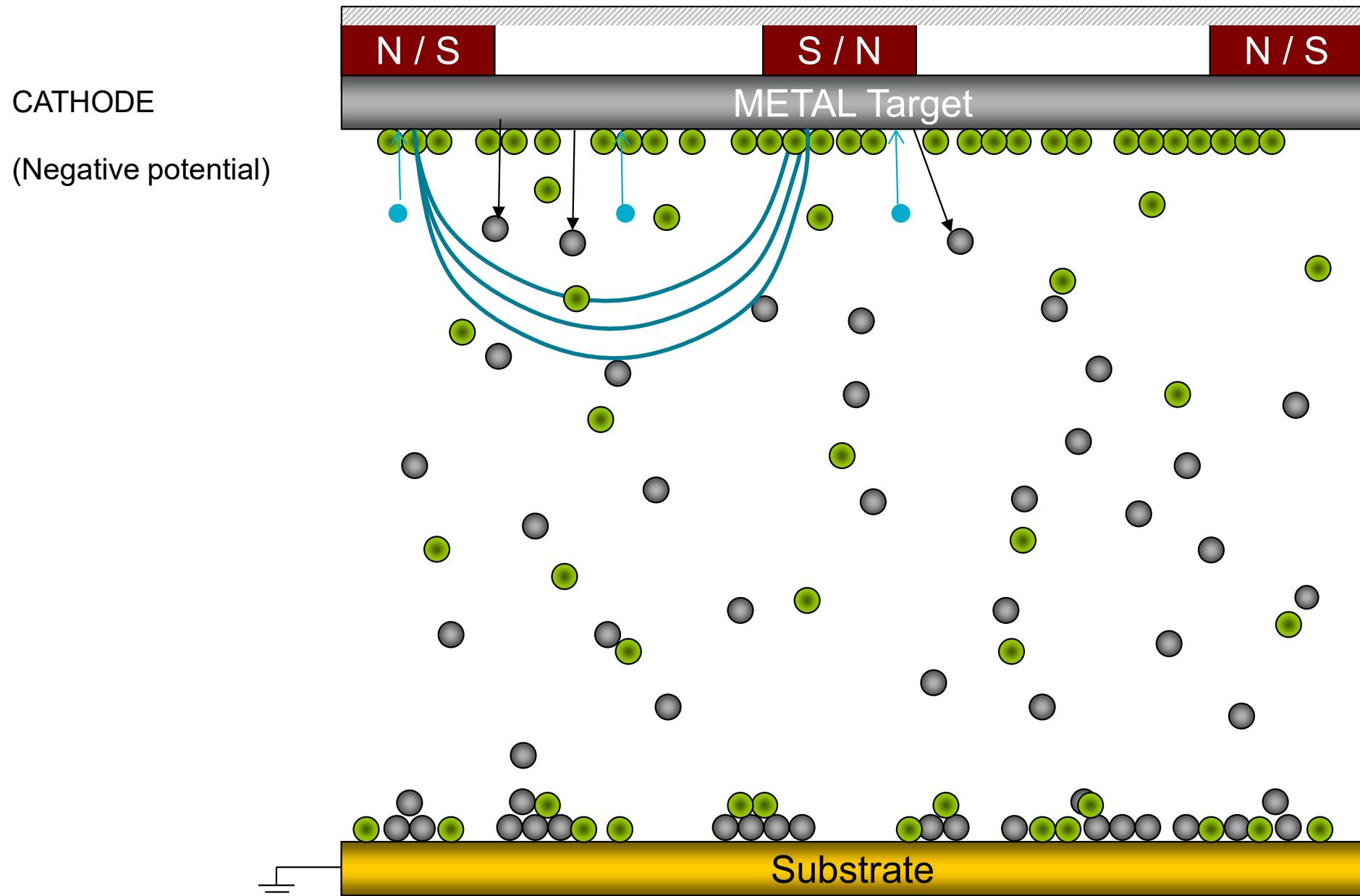


High-Power Impulse Magnetron Sputtering (HiPIMS), From plasma analysis to thin film and nanoparticle synthesis

Conventional DC magnetron sputter deposition

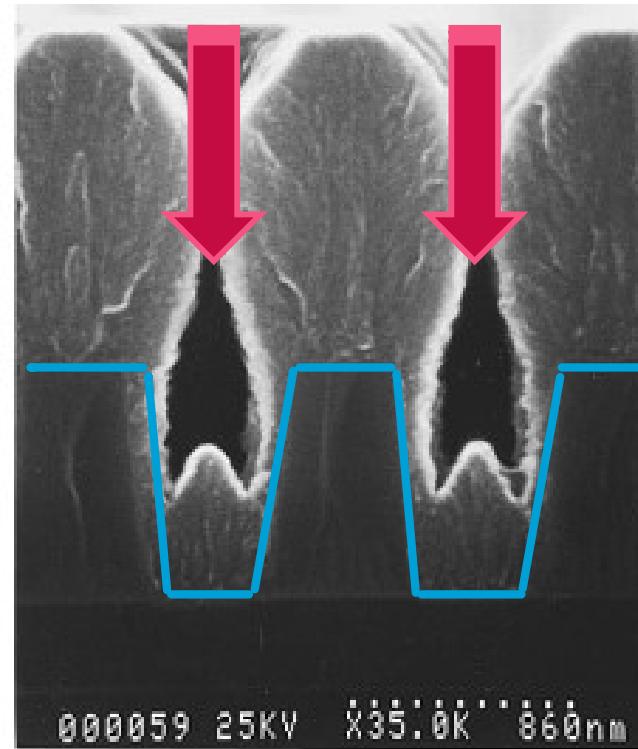


Magnetron sputtering in the (glass) industry



<https://invest.dresden.de/>

Filling trenches by magnetron sputtering



Hamaguchi and Rossnagel, J. Vac. Sci. Technol. (1995).

A black and white close-up photograph of a smiling man. He has dark hair and is wearing a dark suit jacket, a white shirt, and a dark tie. His right hand is raised to his face, with his fingers near his ear and temple. He is looking slightly to the left of the camera with a wide, joyful smile.

The solution:
Let's **ionize**
the sputtered
metal atoms

Advantages brought by the ionization of the sputtered metal atoms

Metal ions (+ negative bias on the substrate) allows :

1. Controlling the **trajectory** of the film – forming species
 - Conformal deposition

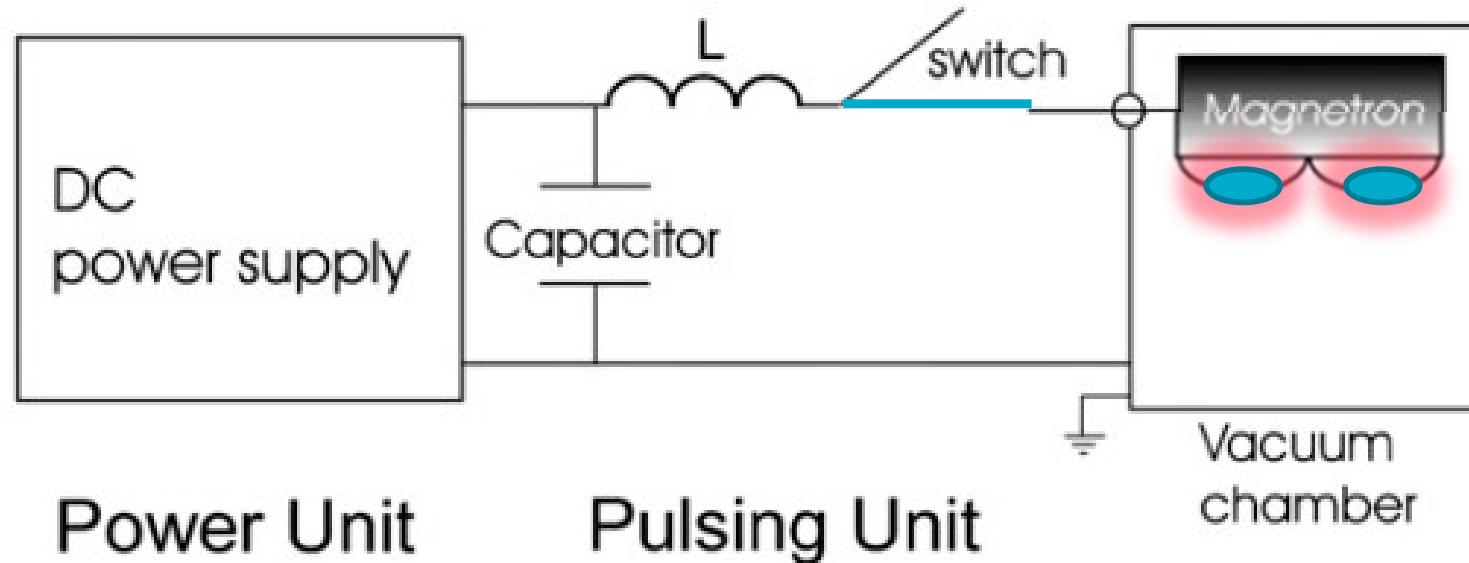
2. Controlling the **kinetic energy** of the film – forming species
 - Crystallinity, micro/nanostructure, roughness,... are modified



How can we
do that ?

- Promote ionization by electron impact
- « Heat » the electrons of the plasma

Architecture of a HiPIMS generator

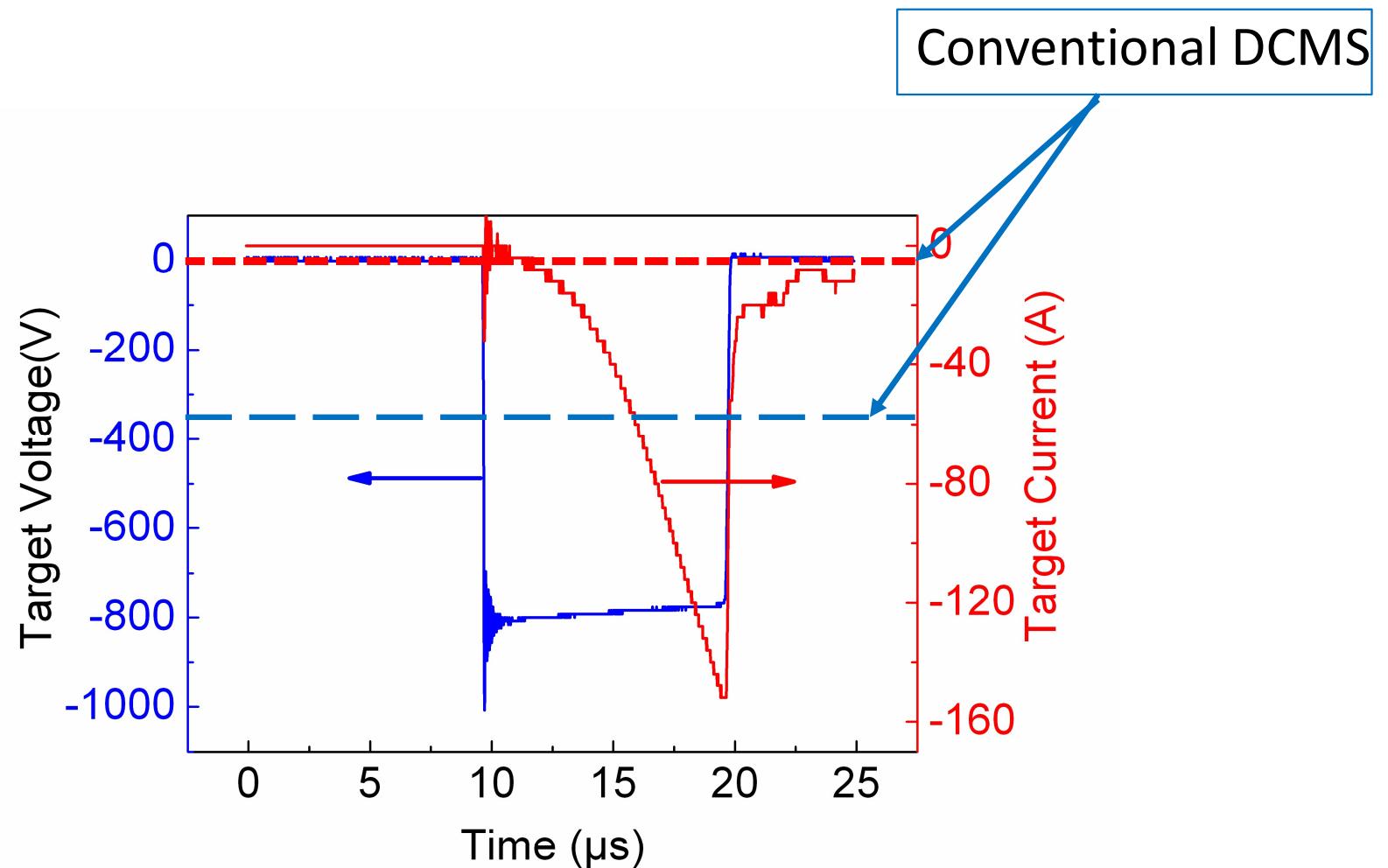


The power supply delivers:

- **Voltage up to 1 – 2 kV**
- Peak current in the range of 10-100 of Amps

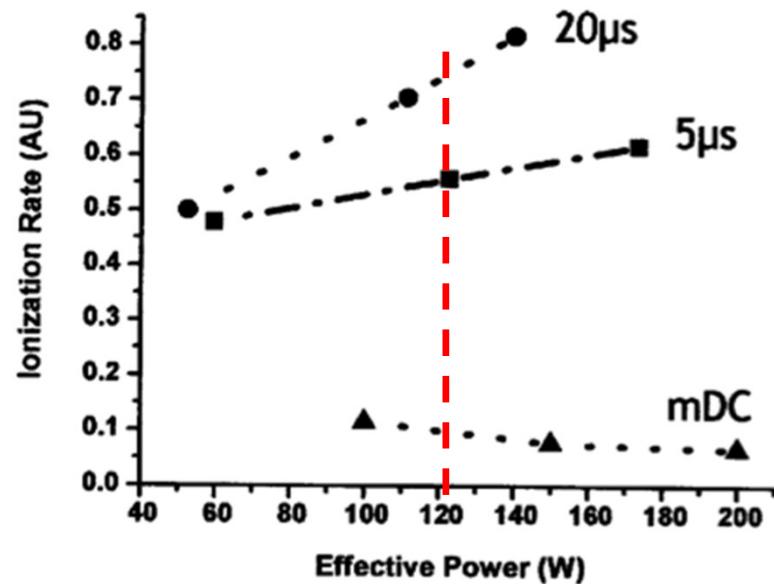
Pulsed discharge to avoid overheating the target/magnets

Typical Current-Voltage-Time waveforms

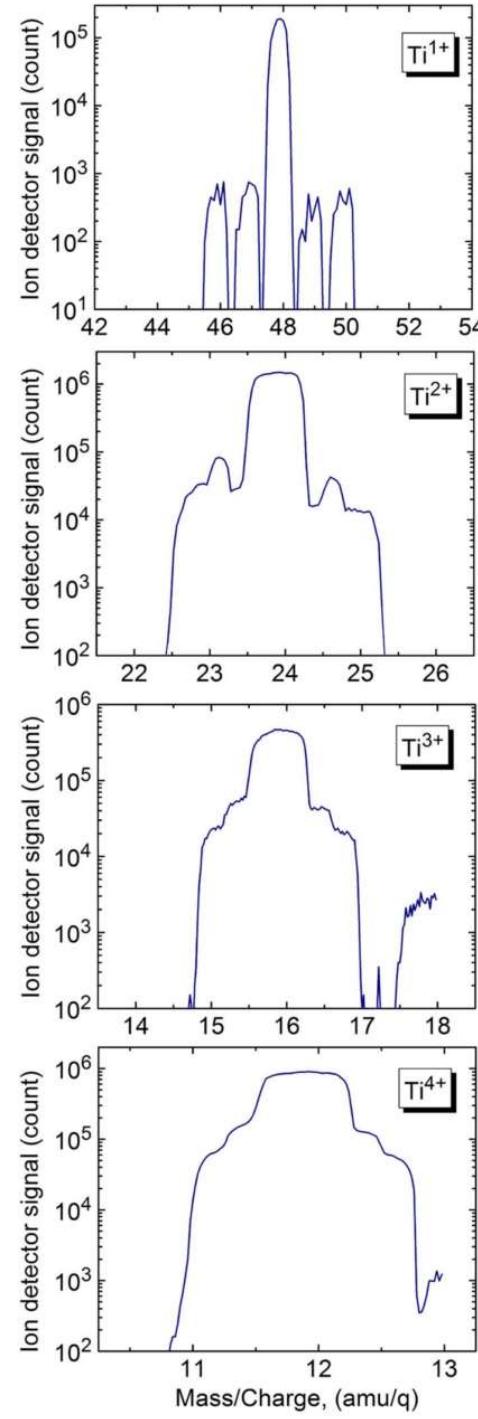


Evidences of the production of metal ionization

Metal ionization rate from AAS measurements



Konstantinidis, J. Appl. Phys. (2006)



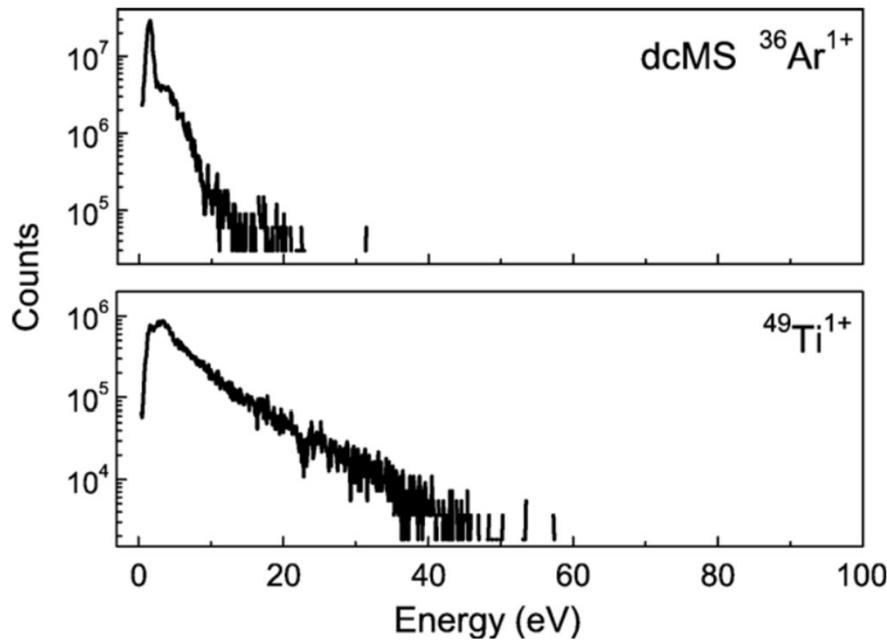
Mass Spec. data

Andersson et al. Appl. Phys. Lett. (2008)

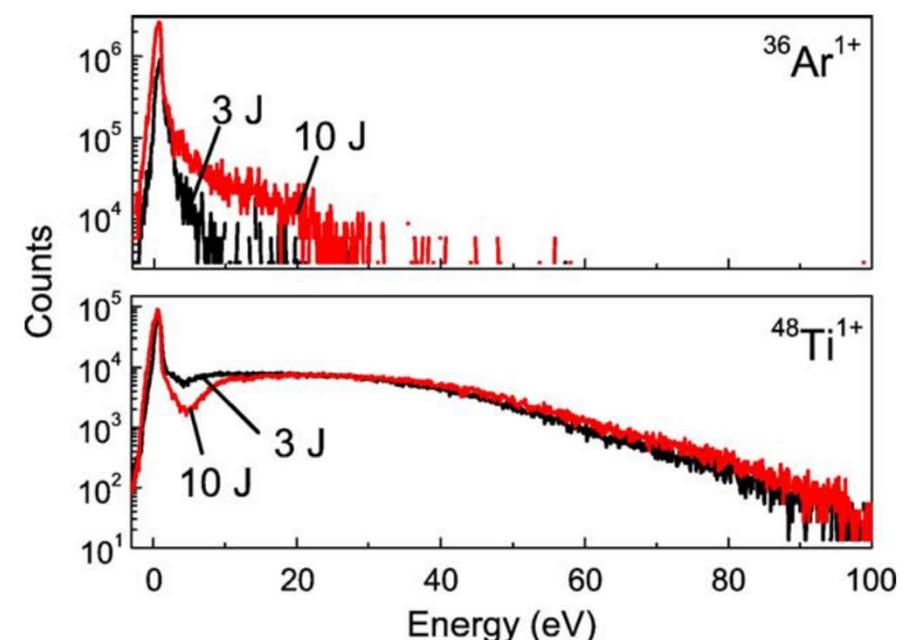
Film – forming species with high kinetic energies

Time-averaged Energy-Resolved Mass spectrometry analysis

DC Magnetron

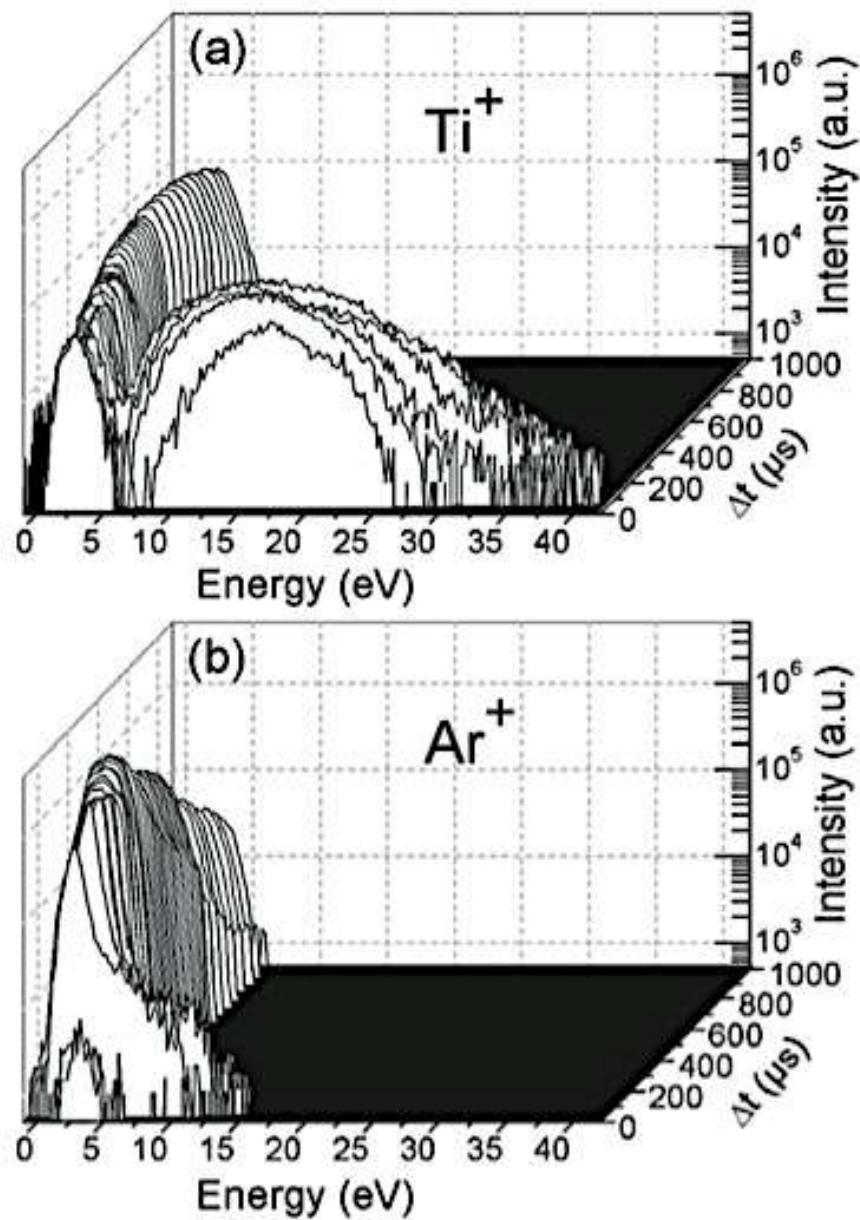


HiPIMS



Bohlmark et al, Thin Solid Films (2006).

Plasma dynamics



Time-Resolved Ion Energy Distribution Functions by
Energy-Resolved Mass Spectrometry analysis

Palmucci et al, J. Phys. D: Appl. Phys. (2013)

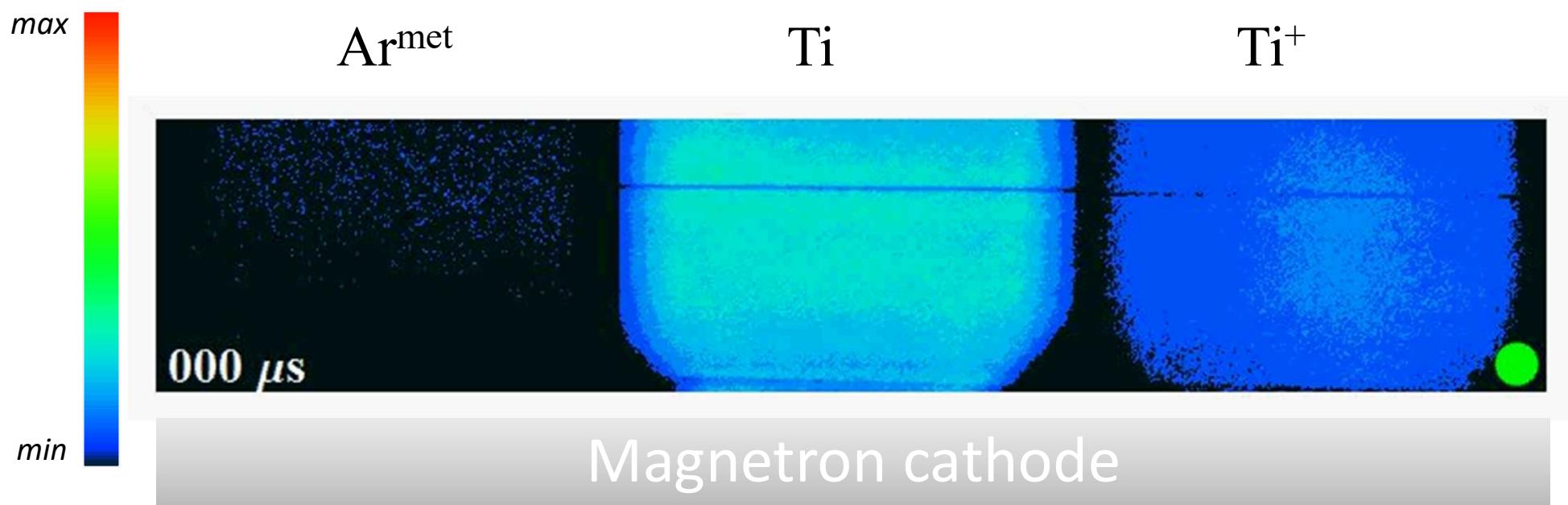
Time & space – dependent plasma chemistry

Time-Resolved 2D mapping of plasma species by LASER induced Fluorescence

Pulse - 20 μ s

Period - 1 ms

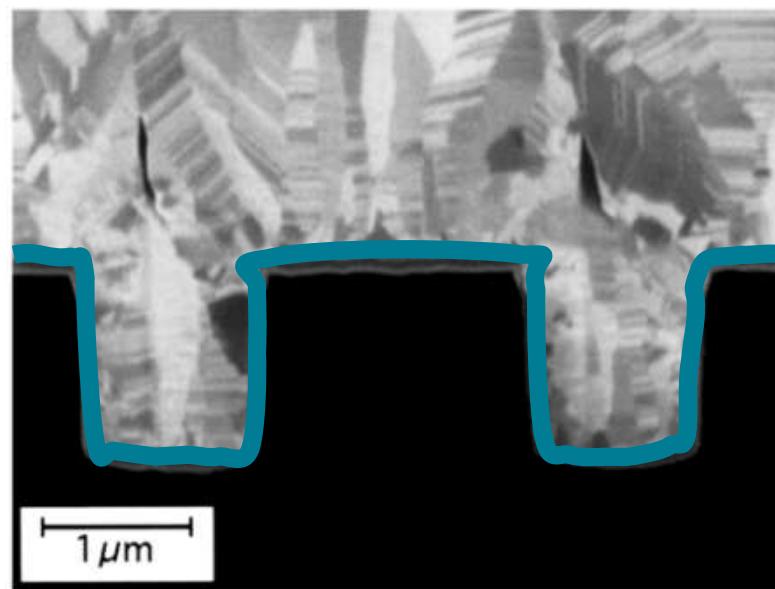
Pressure - 20 mTorr



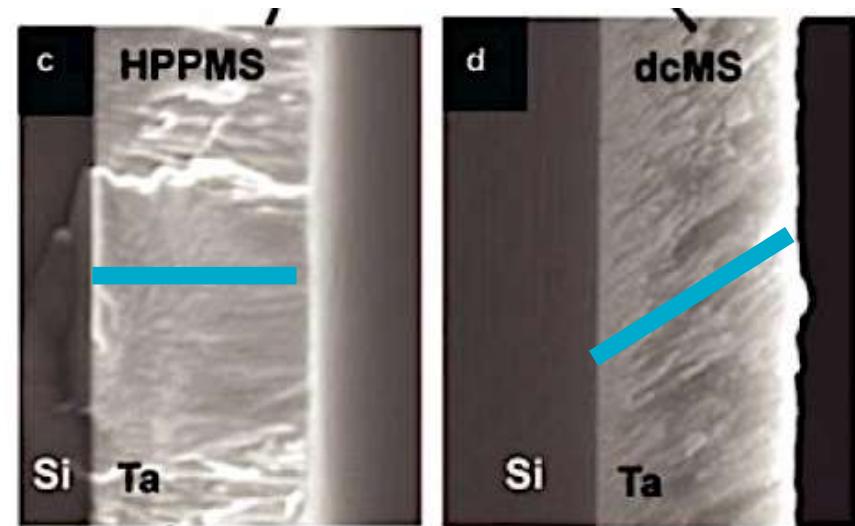
- - *ON-time*
- - *OFF-time*

N. Britun et al, J. Appl. Phys. (2015).

Conformal deposition on complex-shape objects



Substrate surface tilted by 90° vs. target surface



Kouznetsov et al, Surf. Coat. Technol. (1999)

Alami et al, JVST A (2007)

Towards « a definition » of HiPIMS

1. Magnetron plasma

- Glow discharge in ExB fields

2. Electric pulses

- Duty cycle $\leq 1\%$

3. High power/peak current

1. $\sim \text{kW} / \text{A cm}^{-2}$
2. $\Rightarrow N_e \sim 10^{12-13} \text{ cm}^{-3}$

4. High ionization rate of the sputtered material

Some more knobs to tune film properties

- Energy deposition during film growth
- More knobs for tuning the thin film properties
 - Pressure & gas mixture
 - Magnetic & chamber geometry
 - Average power
 - Pulse duration & frequency
 - Pulse voltage

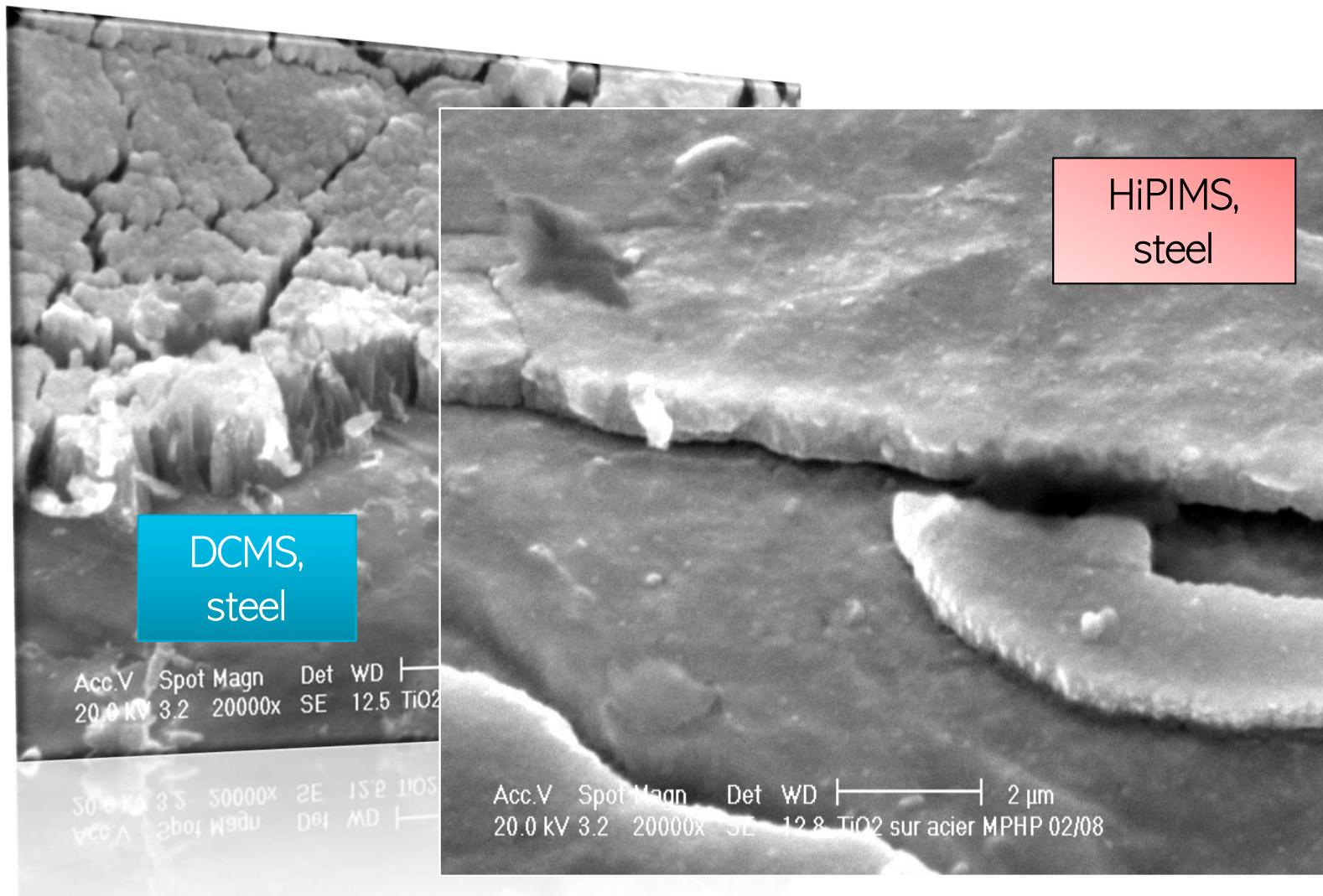


On the synthesis of metal oxide thin films by HiPIMS

1. Titanium dioxide
2. Aluminum-doped zinc oxide
3. Vanadium dioxide

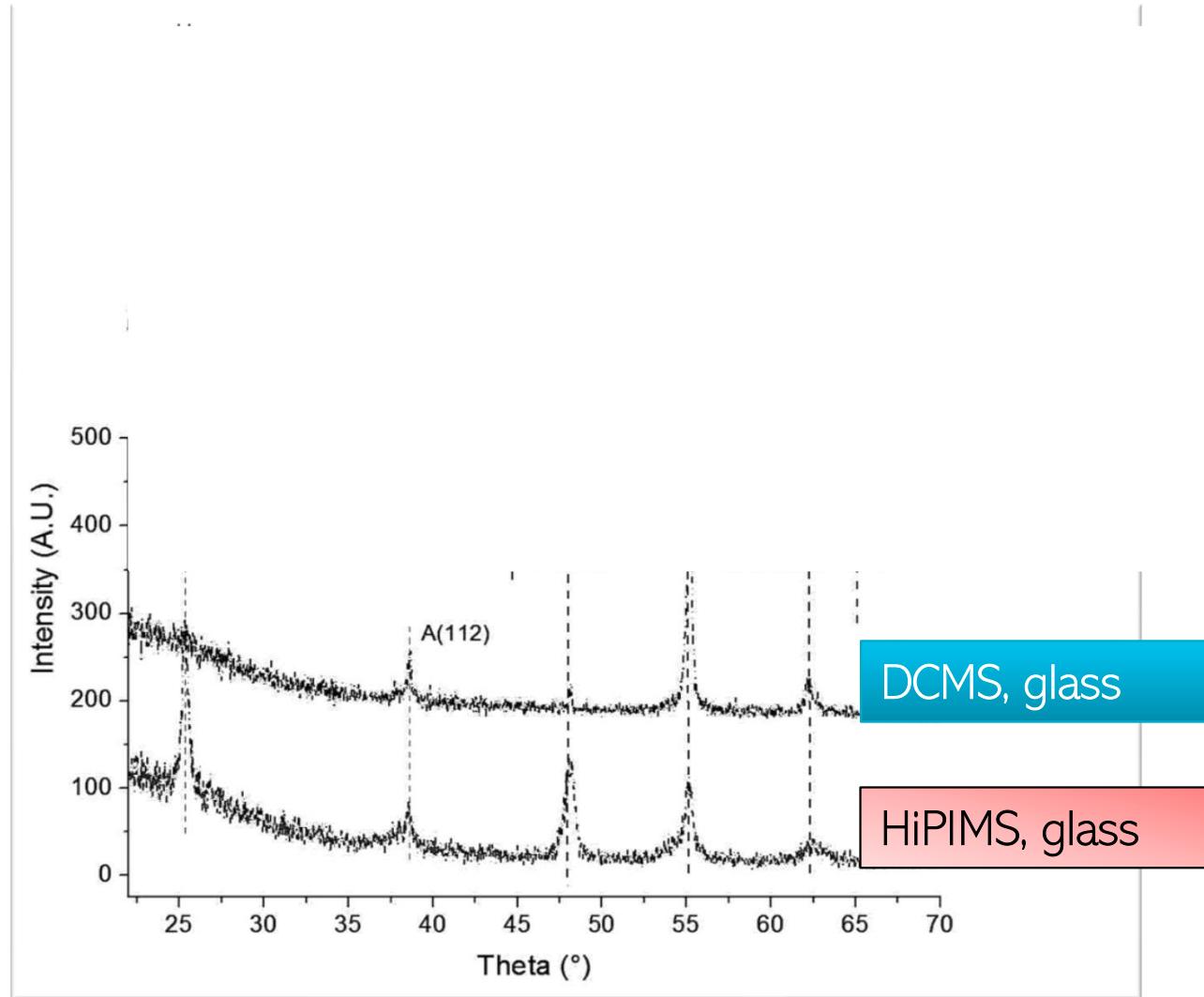
Titanium dioxide

Increased film compactness



Konstantinidis et al, Thin Solid Films (2006)

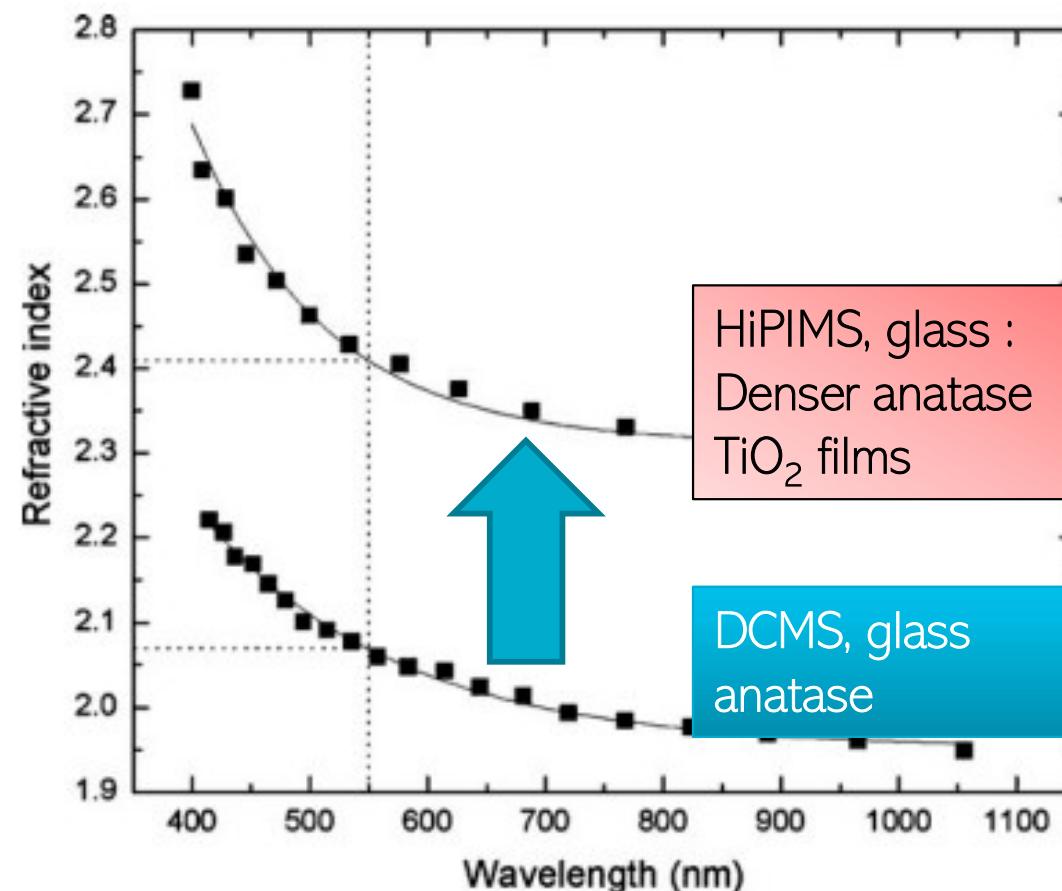
Growing high-temperature phase of TiO_2 by HiPIMS



Konstantinidis et al, Thin Solid Films (2006)

Increased refractive index of TiO_2 films

Anatase films deposited on glass



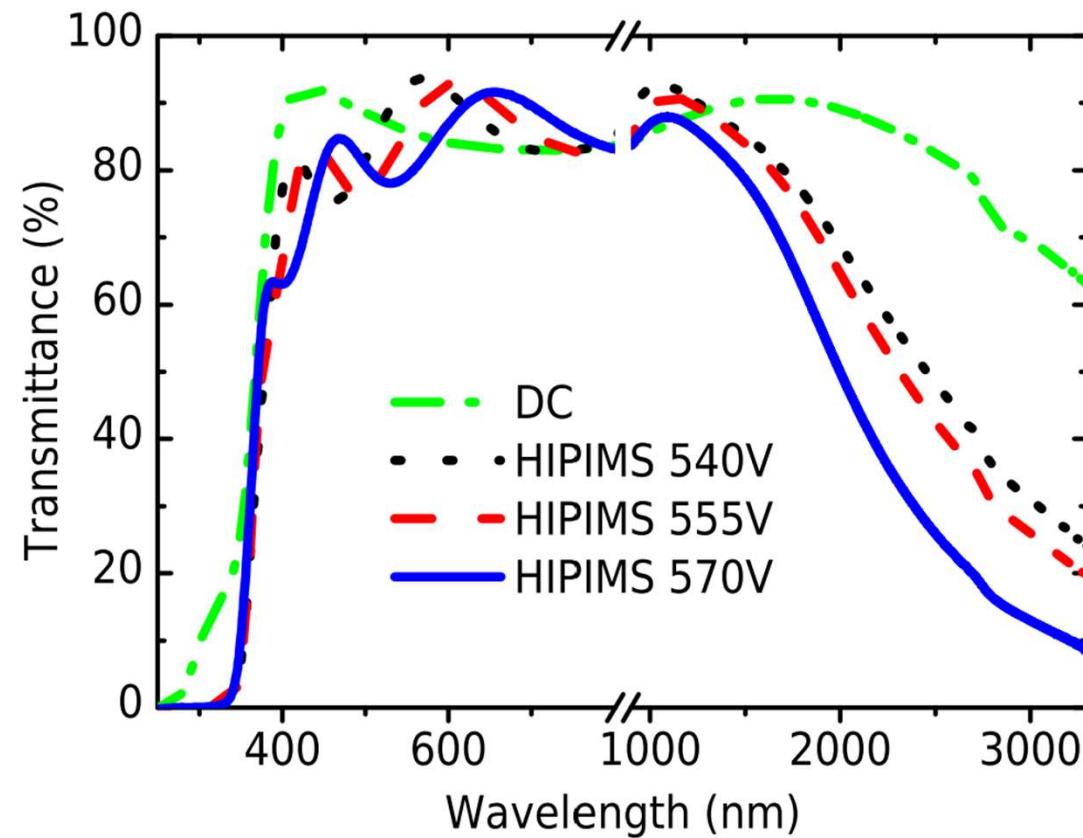
Konstantinidis et al, Thin Solid Films (2006)

Al-doped ZnO

Transmittance of Al-doped ZnO

Sputtering from
an **alloy target** (Zn+Al)
in Ar/O₂ atmosphere

Deposition
at room temperature



Mickan et al, Sol. Energy Mater. Sol. Cells (2016).

Electric properties of ZnO:Al

HiPIMS leads to:

- Low resistivity ($10^{-4} \Omega \text{ cm}$)
- Spatial homogeneity

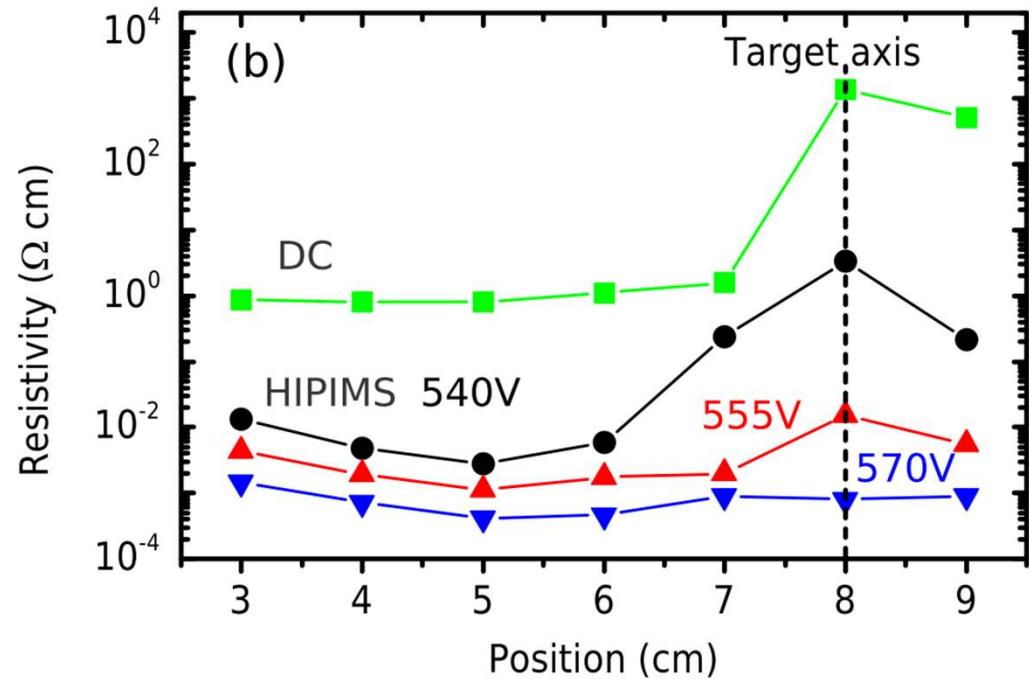


Table S2: Hall effect measurement results of the AZO film deposited using HiPIMS at 570 V

Position (cm)	Resistivity (Ωcm)	Mobility (cm^2/Vs)	Charge carrier concentration (cm^{-3})
3	2.05×10^{-3}	4.09	7.47×10^{20}
4	7.50×10^{-4}	7.38	1.13×10^{21}
5	7.21×10^{-4}	10.5	8.24×10^{20}
6	8.17×10^{-4}	7.07	1.09×10^{21}
7	1.23×10^{-3}	8.84	5.76×10^{20}

Mickan et al, Sol. En. Mater. Sol. Cells (2016).

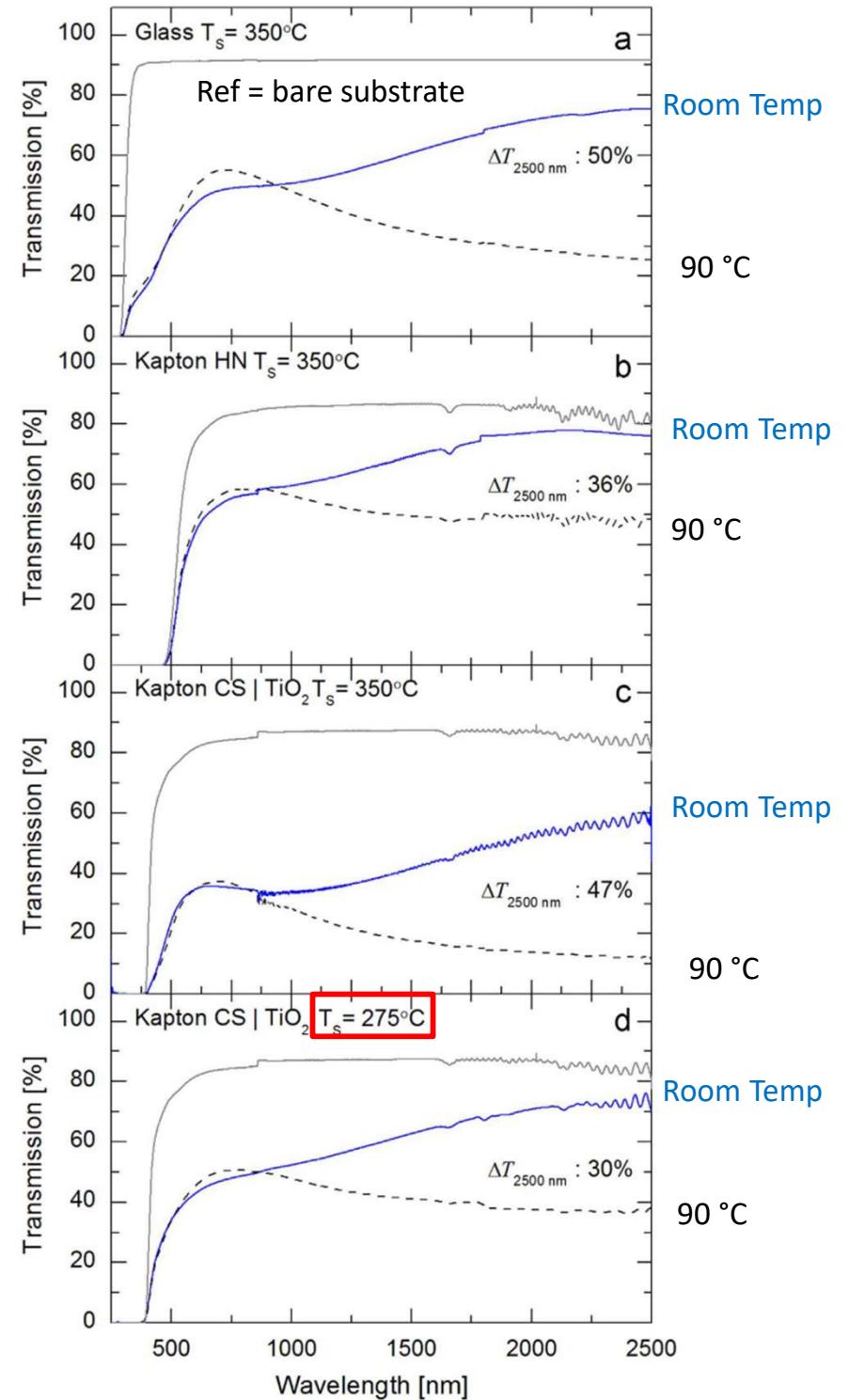
Vanadium dioxide

Synthesis of thermochromic VO_2 at lower temperature

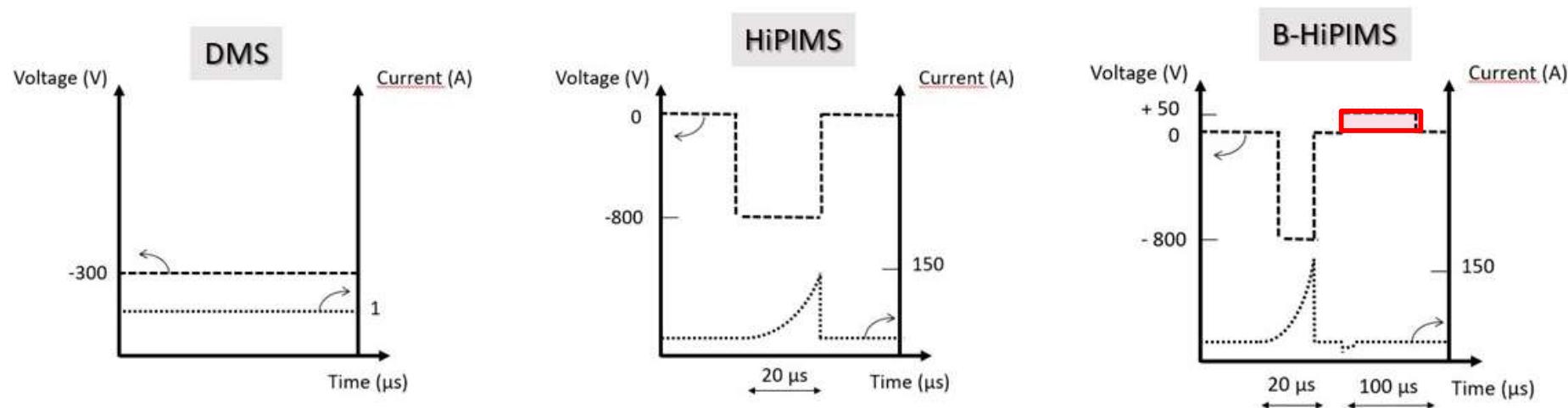
S. Loquai et al, Sol. Energy Mater. Sol. Cells (2016).

Similar results were obtained by

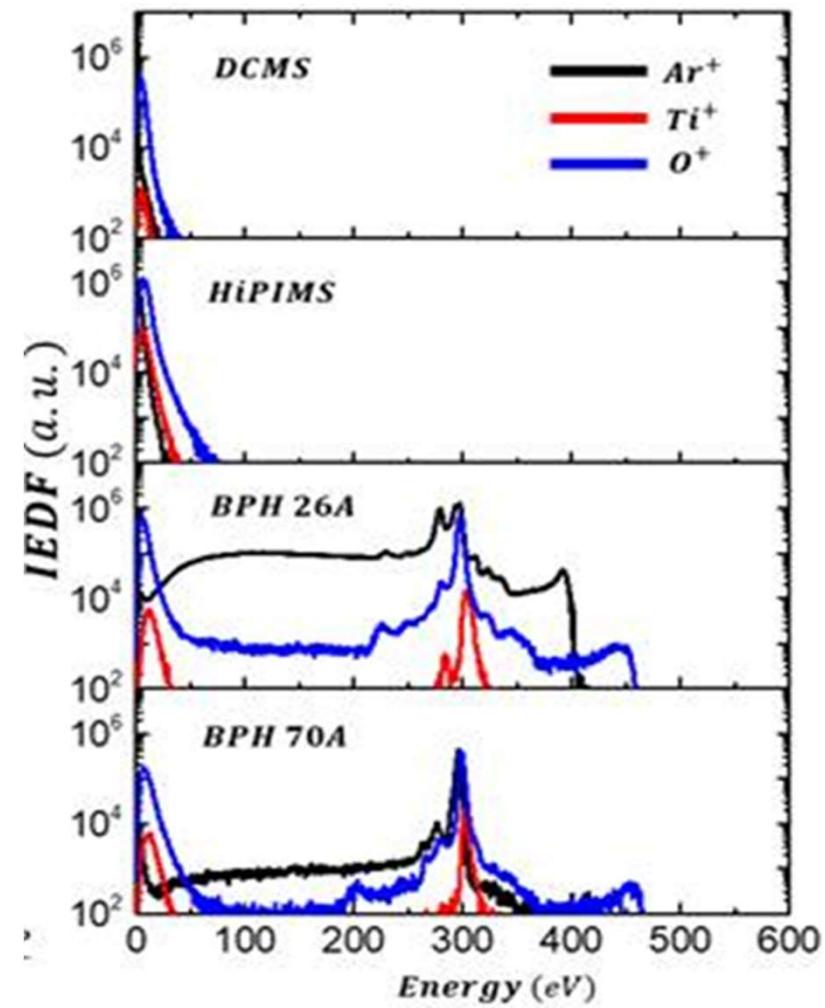
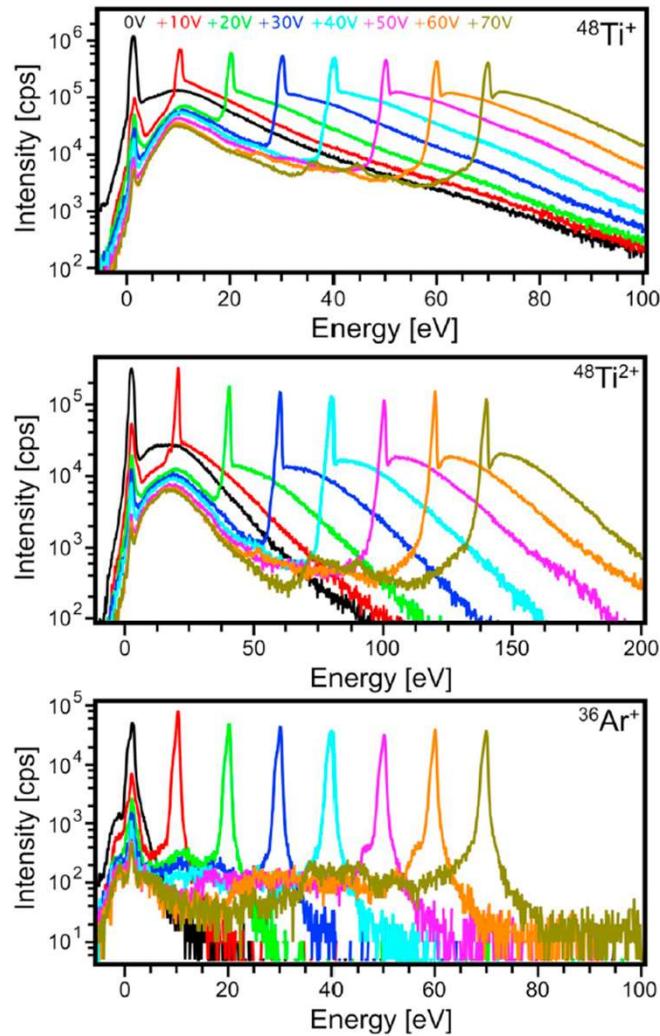
- A. Ajaz et al, Sol. Energy Mater. Sol. Cells (2016).
- J. Houska et al, Thin Solid Films (2018).



Recent development in HiPIMS technology: Bipolar HiPIMS



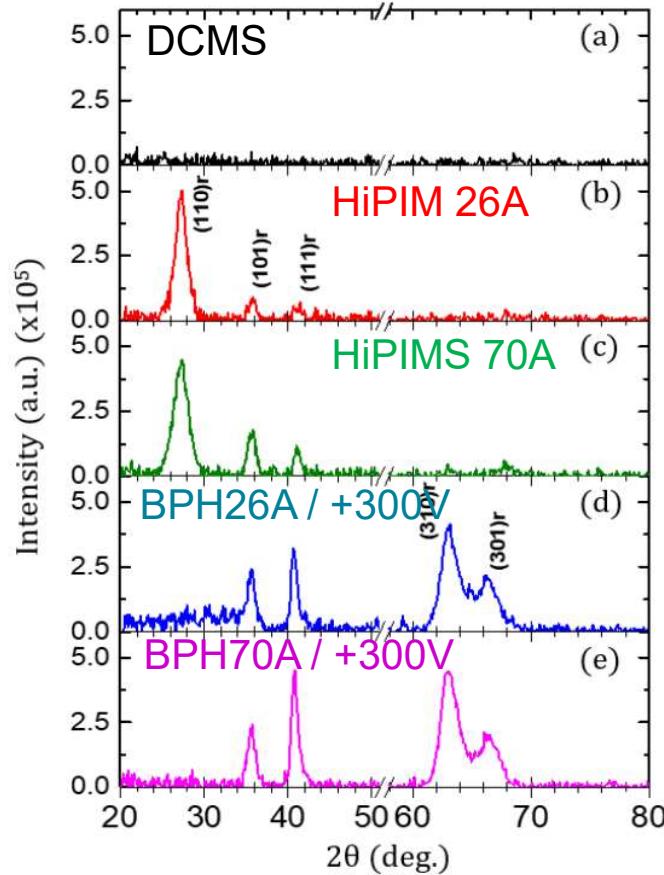
Ion energy is controlled by the positive voltage



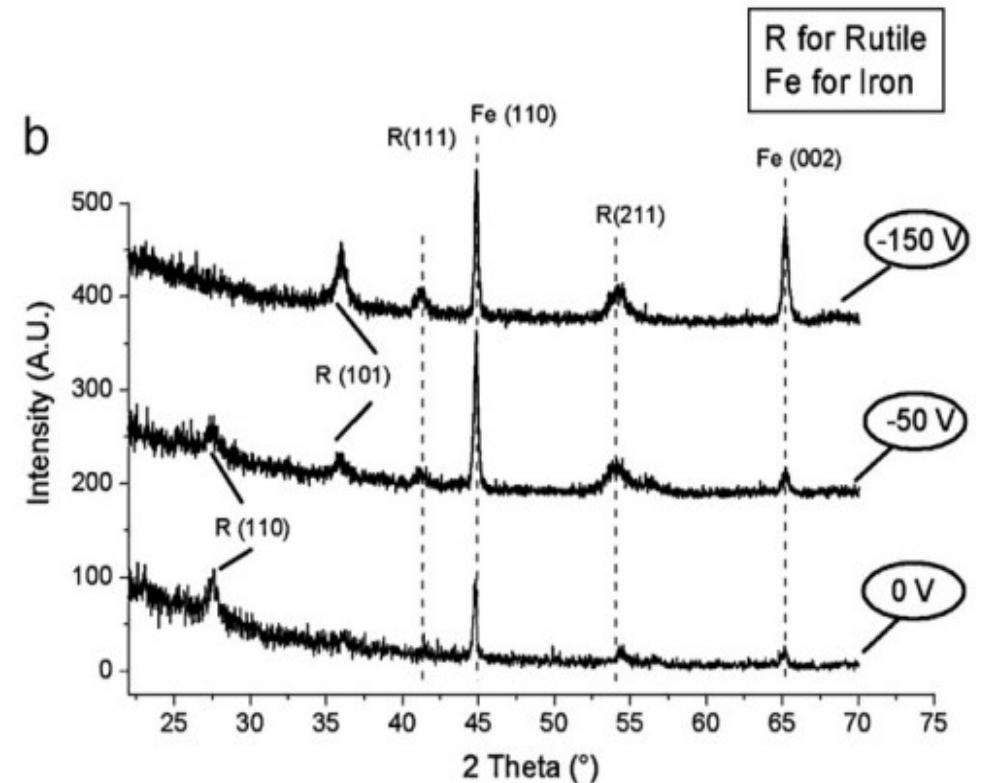
Keraudy et al Surf. Coat. Technol. 2018

Michiels et al, J. Phys. D. Appl. Phys. 2021

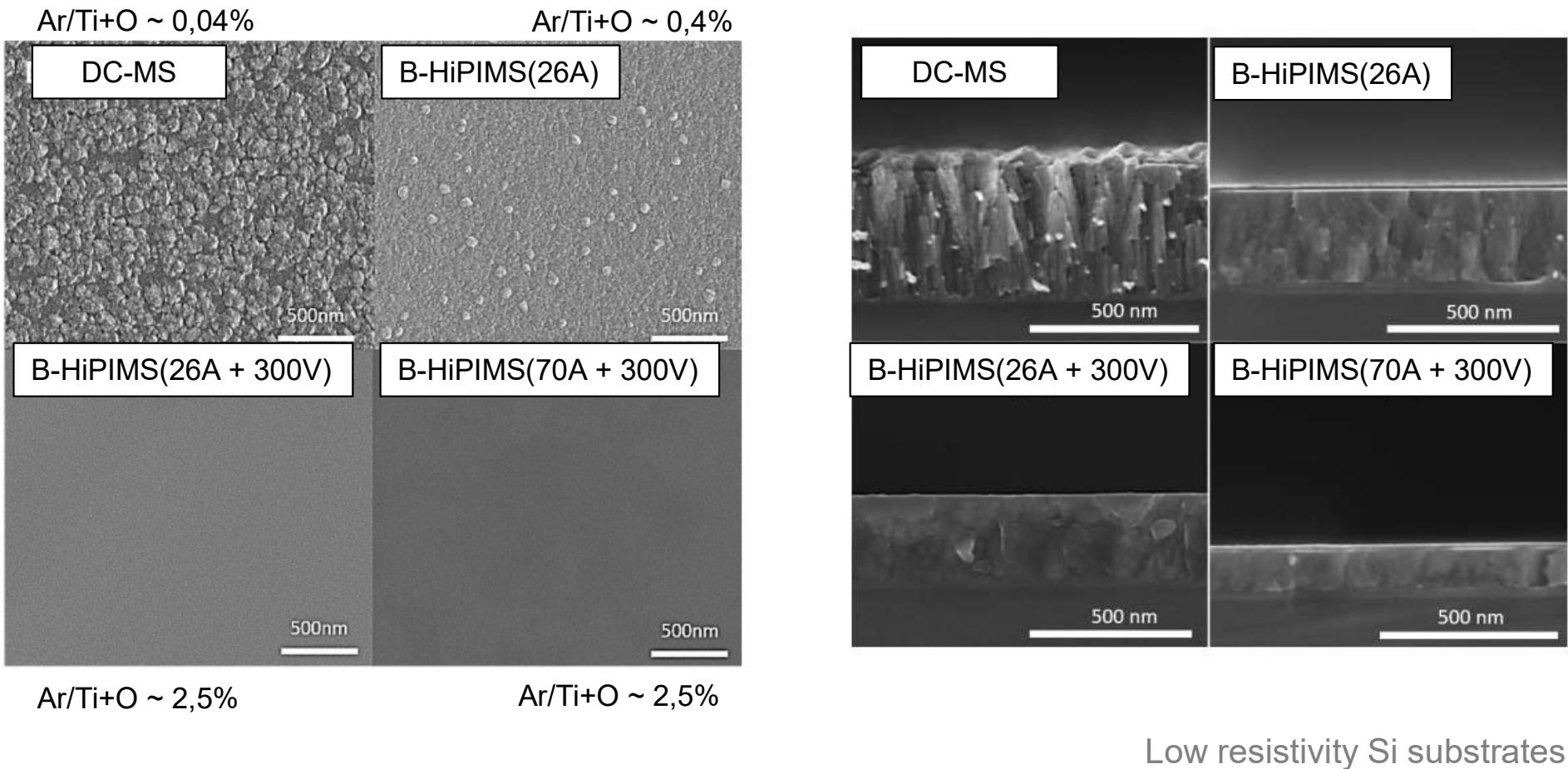
Comparison of the XRD data



Positive pulse on cathode has the same effect as applying a negative bias on the substrate

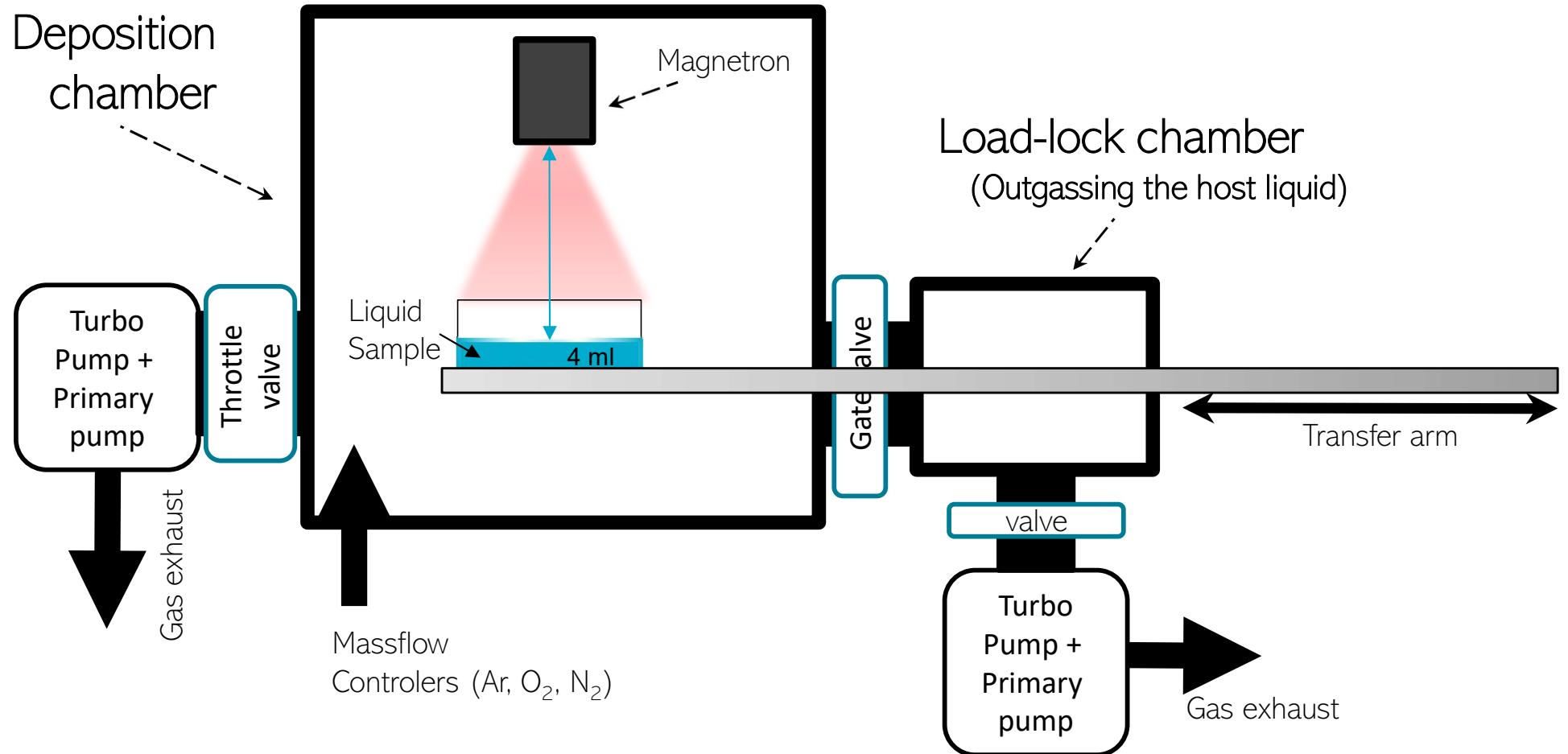


Topography and cross-section

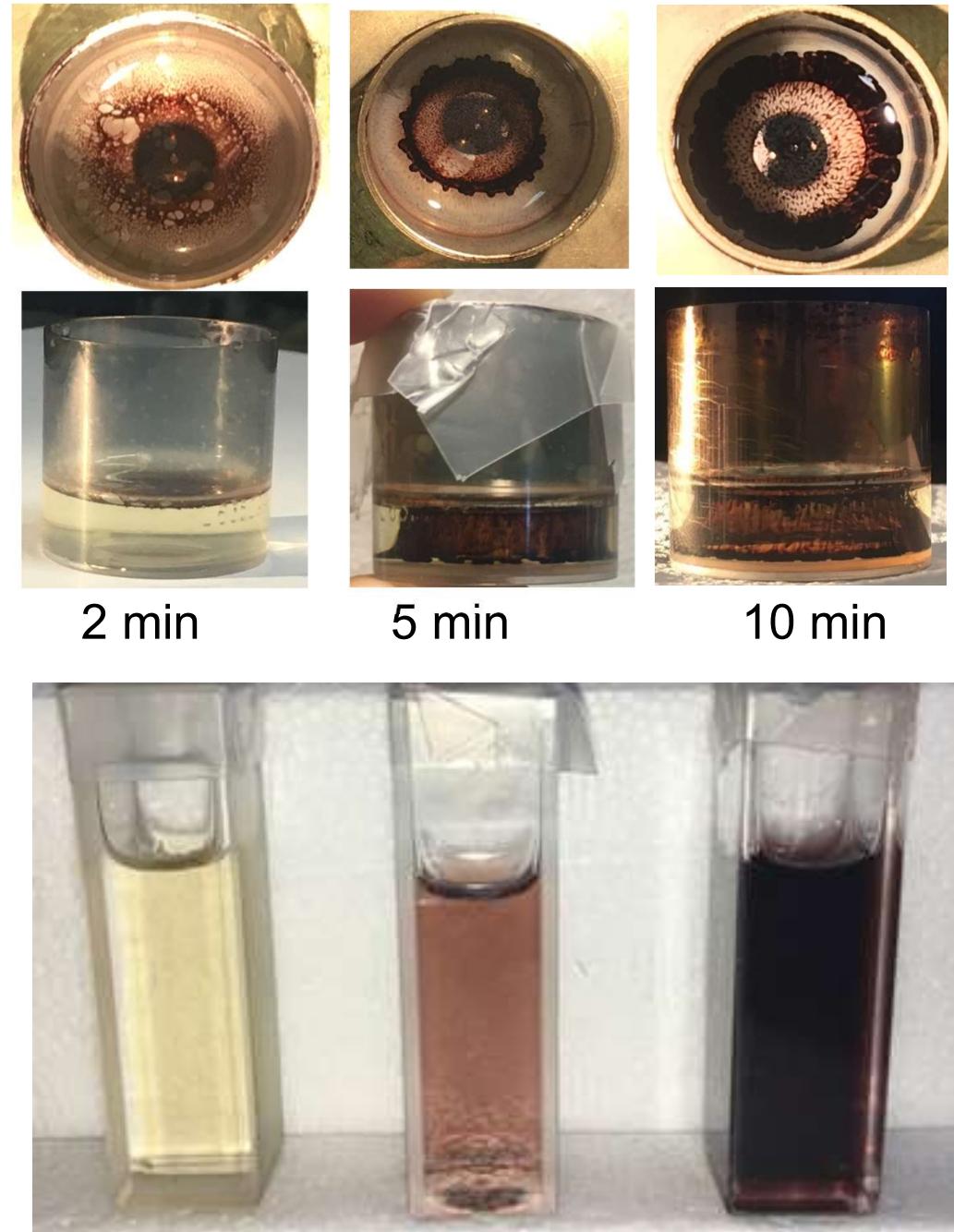


Sputtering onto liquid substrates for the synthesis of nanoparticles

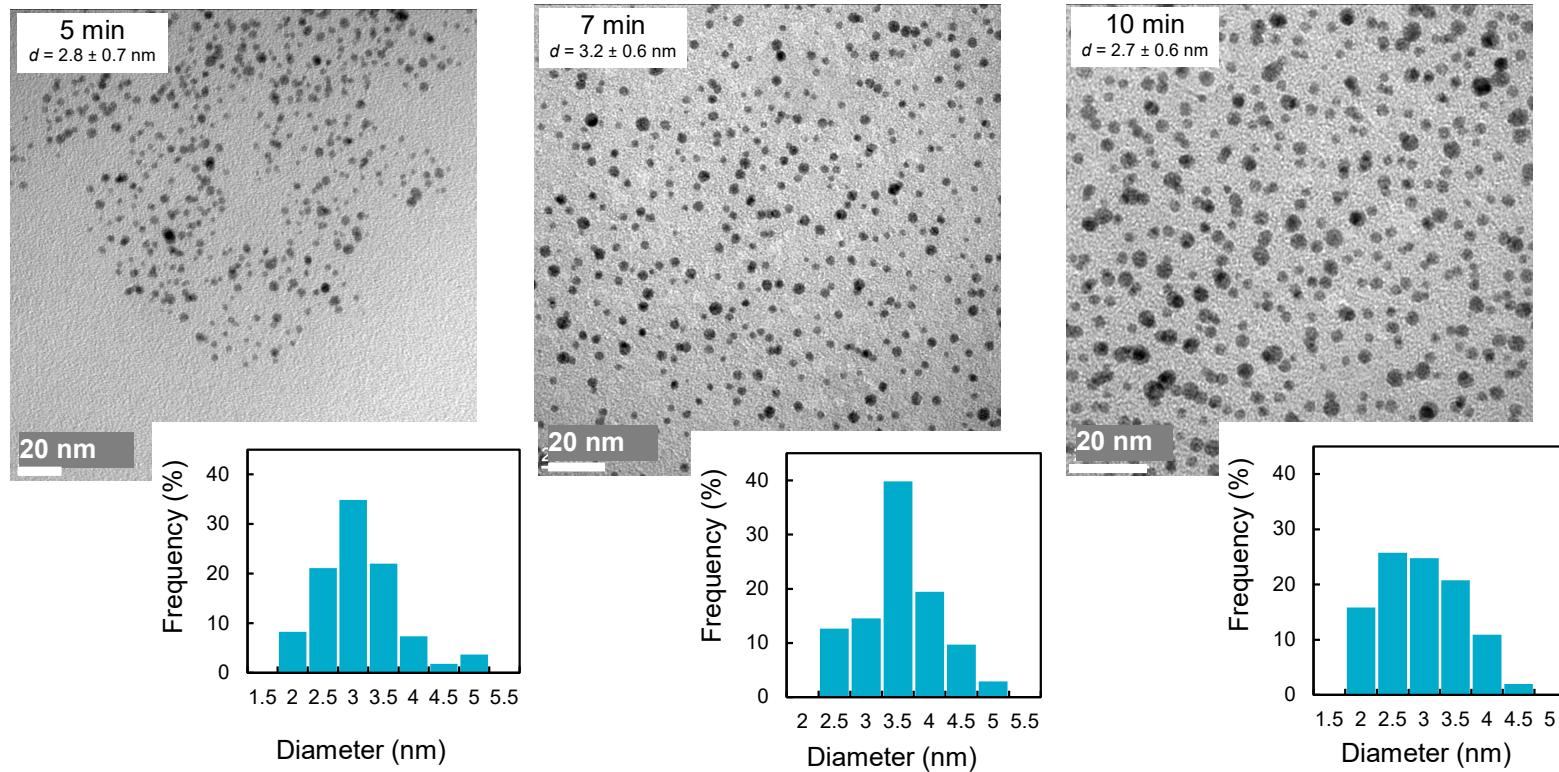
Experimental set-up



DC - Sputtering of Gold on castor oil : Effect of sputter time



TEM observation of the NP



NP size $\sim 2.7 - 3.2 \pm 0.6 \text{ nm}$

Effect of DC sputter power

Sputter time: 10 min

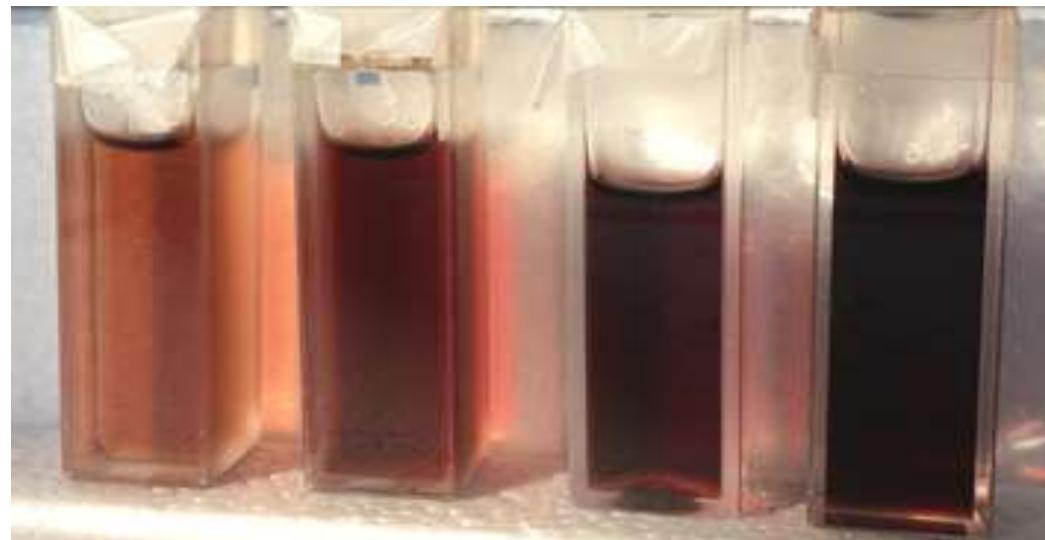


20 W

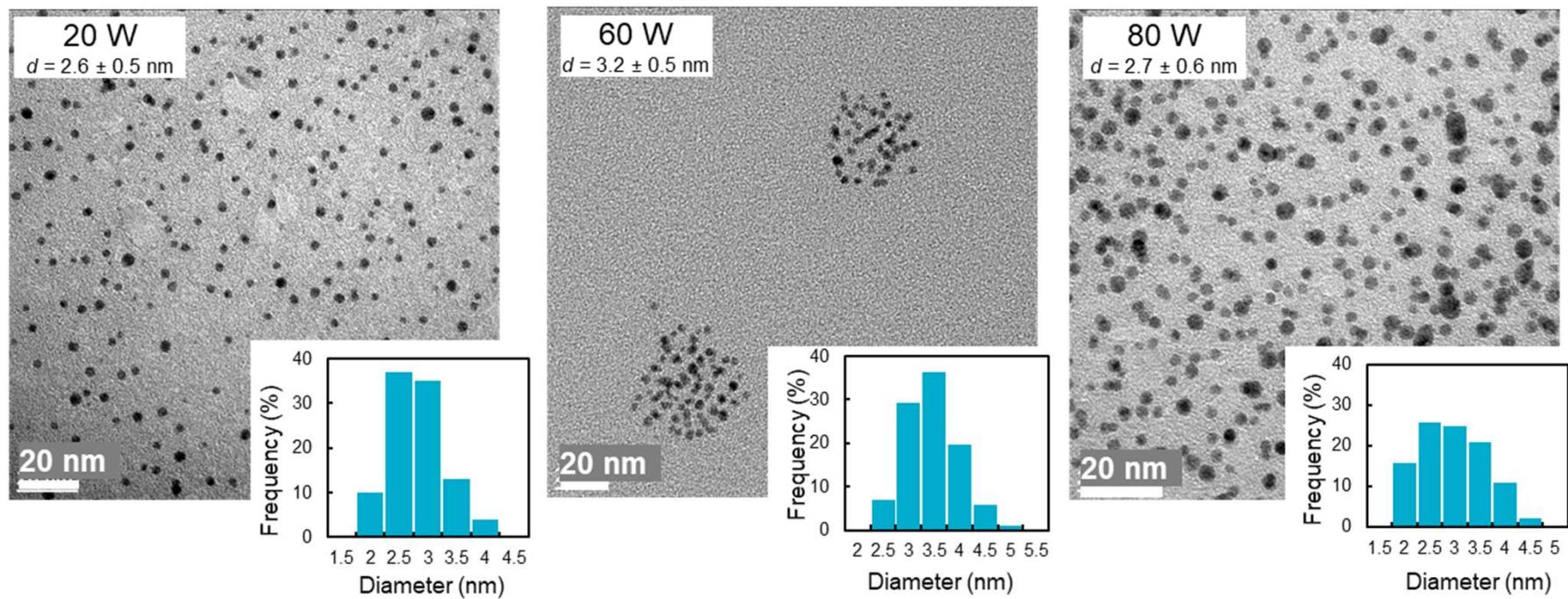
40W

60W

80W



TEM observation of the NP



NP size $\sim 2.7 - 3.2 \pm 0.5 \text{ nm}$

DC-MS vs. (unipolar) HiPIMS

$P_{Ar} = 5 \text{ mTorr}$, 80 W, 10 min

DC-MS:

$$\Phi = (1.8 \pm 0.2) \cdot 10^{-7} \text{ moles/cm}^2 \cdot \text{min}$$

HiPIMS:

$$T_{on} = 20 \mu\text{s}, I_{pk} = 0.3 \text{ A/cm}^2, f = 800 \text{ Hz},$$
$$\Phi = (0.9 \pm 0.1) \cdot 10^{-7} \text{ moles/cm}^2 \text{ min}$$

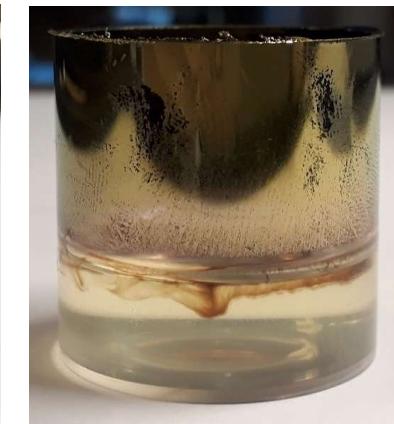
DC-MS



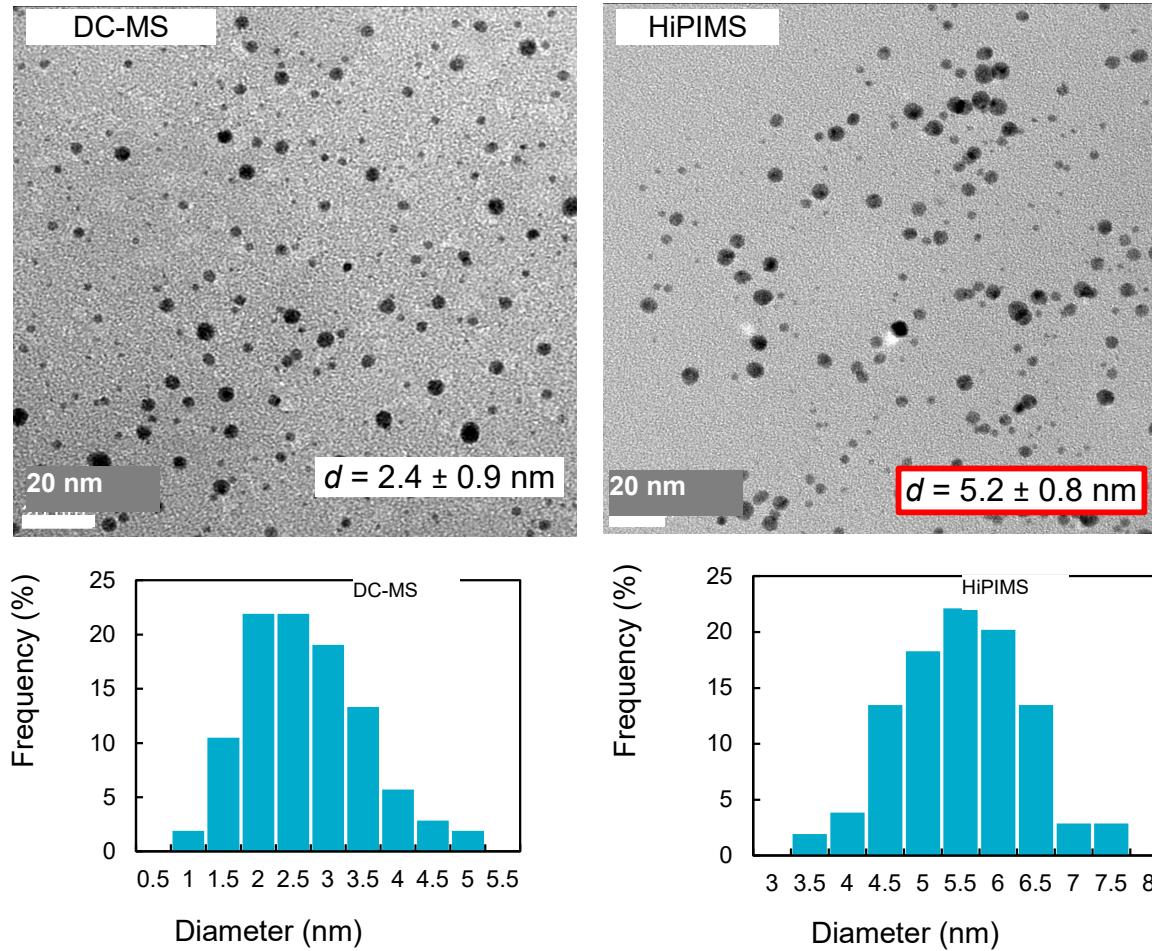
HiPIMS



DC-MS HiPIMS



TEM analysis of the NP



NP size is increased when produced by HiPIMS plasma

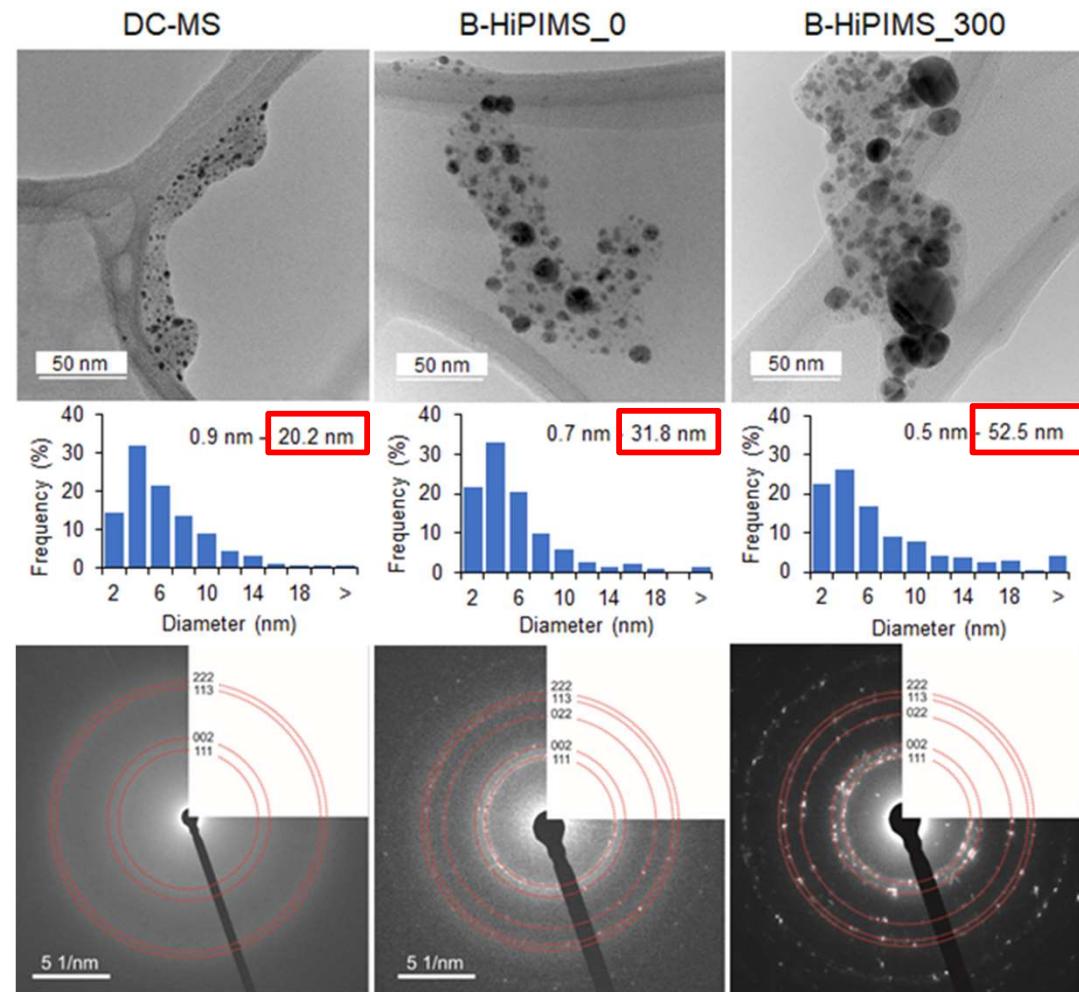
Silver onto castor oil : DC-MS vs. Unipolar & Bipolar HiPIMS

$P_{Ar} = 5 \text{ mTorr}$, 80 W, 10 min

Flux DC-MS: $(1.8 \pm 0.2) \cdot 10^{-7} \text{ moles/cm}^2 \text{ min}$

Flux HiPIMS: $(0.9 \pm 0.1) \cdot 10^{-7} \text{ moles/cm}^2 \text{ min}$
 $f = 800 \text{ Hz}$, $T_{ON,-} = 20 \mu\text{s}$, $I_{pk} = 0.3 \text{ A/cm}^2$

Flux B-HiPIMS: $(0.2 \pm 0.1) \cdot 10^{-7} \text{ moles/cm}^2 \text{ min}$
 $f = 800 \text{ Hz}$, $T_{ON,-} = 20 \mu\text{s}$, $I_{pk} = 0.3 \text{ A/cm}^2$
 $V_+ = +300V$, $T_{ON,+} = 250 \mu\text{s}$, $T_{+/-} = 10\mu\text{s}$



Number of particles larger than 20 nm

- 0.1% for DC-MS,
- 1.3 % for HiPIMS (B-HiPIMS_0)
- 4.2 % for bipolar HiPIMS (BHiPIMS_300)

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Sergievskaya et al, Colloids Surf. A **615**, 126286 (2021).

Summary

1. HiPIMS modifies the growth process and film properties
 - Increased density
 - Modified crystallinity (high-temp. phase, texture, crystallite size)
 - Lower roughness
2. HiPIMS may facilitate the deposition of functional films onto temperature sensitive materials like polymers
3. Recent developments e.g., bipolar HiPIMS, aim at providing even more control on the film growth process
4. Sputtering can be carried out onto selected liquids to produce colloidal solutions.
 - HiPIMS mimics *in situ* annealing procedure of the NPs